



#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Features**

- Dual N-Channel MOSFET
- Low On-Resistance (1.0V Max)
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected up to 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

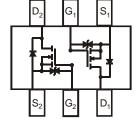
### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe.
   Solderable per MIL-STD-202, Method 208 \$\mathbb{G}\$
- Weight: 0.006 grams (Approximate)

**SOT363** 







Top View

Top View Internal Schematic

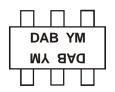
# **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMN5L06DWK-7	SOT363	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



DAB = Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Date Code Ney												
Year	2006	2007	2008		2012	2013	2014	2015	2016	2017	2018	2019
Code	Т	U	V		Z	Α	В	С	D	E	F	G
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code		_	_									)

March 2017



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain Source Voltage	$V_{DSS}$	50	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Drain Current Continuous Pulsed (Note 6)	I <sub>D</sub>	305 800	mA	

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_{D}$	250	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	500	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

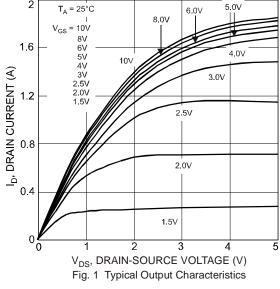
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

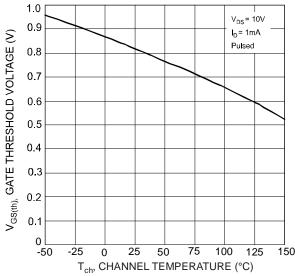
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)					I.	l.		
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	50	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current	@ T <sub>C</sub> = +25°C	I <sub>DSS</sub>	_	_	60	nA	$V_{DS} = 50V, V_{GS} = 0V$	
					1	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$	
Gate-Body Leakage		$I_{GSS}$	_	_	500	nΑ	$V_{GS} = \pm 10V$ , $V_{DS} = 0V$	
					50	nA	$V_{GS} = \pm 5V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage		$V_{GS(TH)}$	0.49		1.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
			_	_	3.0		$V_{GS} = 1.8V, I_D = 50mA$	
Static Drain-Source On-Resistance		R <sub>DS(ON)</sub>	_	_	2.5	Ω	$V_{GS} = 2.5V, I_D = 50mA$	
			_	_	2.0		$V_{GS} = 5.0V, I_D = 50mA$	
On-State Drain Current		$I_{D(ON)}$	0.5	1.4	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$	
Forward Transconductance		Y <sub>FS</sub>	200	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$	
Source-Drain Diode Forward Voltage		$V_{SD}$	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance		C <sub>ISS</sub>	_	_	50	pF	)/ 25)/ )/ 0)/	
Output Capacitance		Coss	_	_	25	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance		C <sub>RSS</sub>	_	_	5.0	pF	1 = 1.000112	
Gate Resistance		$R_G$	_	65	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge		$Q_{G}$	_	0.4	_	nC	$V_{GS} = 4.5V V_{DS} = 10V,$ $I_{D} = 0.25A$	
Gate-Source Charge		$Q_{GS}$	_	0.1	_	nC		
Gate-Drain Charge		$Q_{GD}$	_	0.1	_	nC		
Turn-On Delay Time		t <sub>D(ON)</sub>	_	2.1	_	ns		
Turn-On Rise Time		t <sub>R</sub>	_	1.8	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$	
Turn-Off Delay Time				$R_G = 25\Omega, I_D = 0.2A$				
Turn-Off Fall Time		t <sub>F</sub>		8.4		ns		

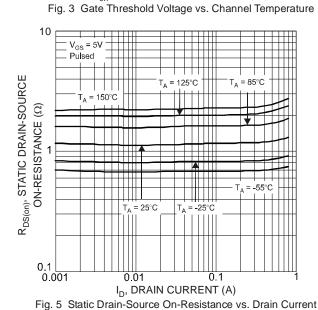
Notes:

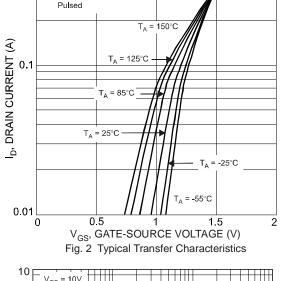
- 5. Device mounted on FR-4 PCB.
- 6. Pulse width ≤10µS, Duty Cycle ≤1%.
  7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.











0.4

 $V_{DS} = 10V$ 

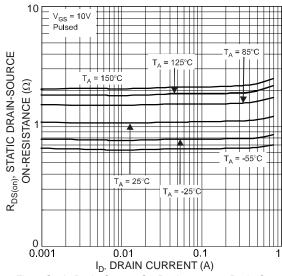


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

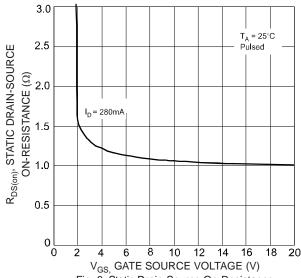


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage



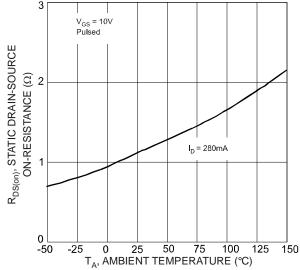


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

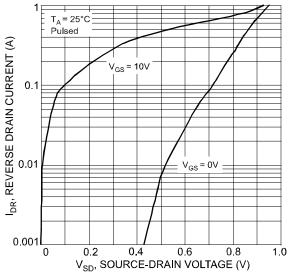
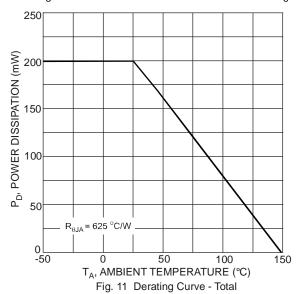


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage



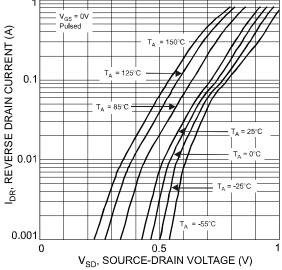


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

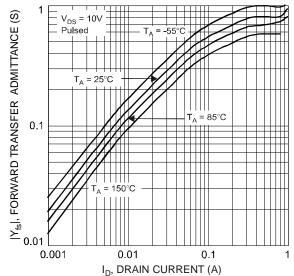


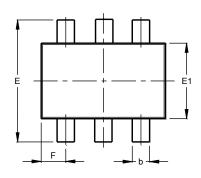
Fig.10 Forward Transfer Admittance vs. Drain Current

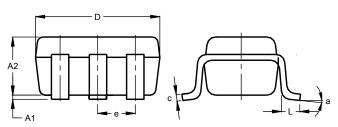


# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT363**



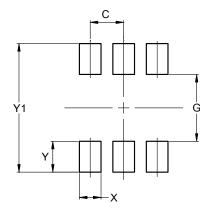


SOT363						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	1.00			
b	0.10	0.30	0.25			
C	0.10	0.22	0.11			
D	1.80	2.20	2.15			
Е	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
e	0.650 BSC					
F	0.40	0.45	0.425			
L	0.25	0.40	0.30			
а	0°	8°				
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT363**



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Y	0.600
Y1	2.500



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